

TO-18 Plastic-Encapsulate Transistors

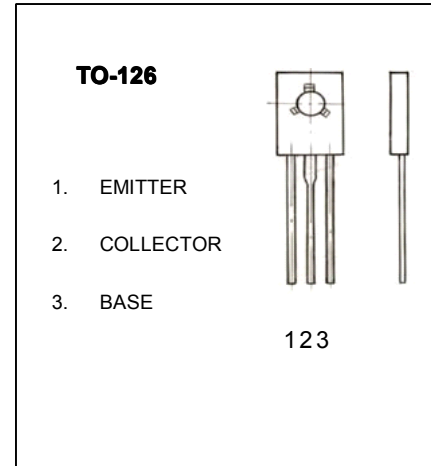
B772 TRANSISTOR (PNP)

FEATURES

Low speed switching

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current -Continuous	-3	A
P _D	Collector Power Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	I _C = 100μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C = 10mA, I _B =0	-30			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = 100μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} = 40 V, I _E =0			-1	μA
Collector cut-off current	I _{CEO}	V _{CE} = 30 V, I _B =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 6 V, I _C =0			-1	μA
DC current gain	h _{FE}	V _{CE} = 2 V, I _C = 1A	60		400	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 2A, I _B = 0.2 A			-0.5	V
Base-emitter saturation voltage	V _{BE (sat)}	I _C = 2A, I _B = 0.2 A			-1.5	V
Transition frequency	f _T	V _{CE} = 5V, I _C =0.1A f =10MHZ		90		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400